

N-channel 40 V 1.55 mΩ logic level MOSFET in LFPAK using NextPower technology

22 August 2012

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 150°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	-	40	V
ID	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	288	W
Tj	junction temperature			-55	-	150	°C
Static chara	acteristics	1	I				
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12		-	1.45	1.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12		-	1.25	1.55	mΩ
Dynamic cl	haracteristics	1	1				
Q _{GD}	gate-drain charge	V_{GS} = 4.5 V; I _D = 25 A; V _{DS} = 20 V; Fig. 14		-	15.3	-	nC



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I _D = 25 A; V _{DS} = 20 V; Fig. 14	-	59	-	nC

[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G-UF 44
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain		
			LFPAK; Power- SO8 (SOT1023)	

3. Ordering information

Table 3.	Ordering information	

Type number	Package	•				
	Name	Description	Version			
PSMN1R6-40YLC	LFPAK; Power-SO8	Plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT1023			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 150 °C		-	40	V
V _{DGR}	drain-gate voltage	25 °C \leq T _j \leq 150 °C; R _{GS} = 20 k Ω		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	100	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	[1]	-	100	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 4		-	1304	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	288	W
T _{stg}	storage temperature			-55	150	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Tj	junction temperature			-55	150	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		1	-	kV
Source-drain	diode	!	1			
l _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1304	А
Avalanche ru	lggedness	!	1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 100 A; V _{sup} ≤ 40 V; R _{GS} = 50 Ω; unclamped; Fig. 3		-	391	mJ

[1] Continuous current is limited by package.

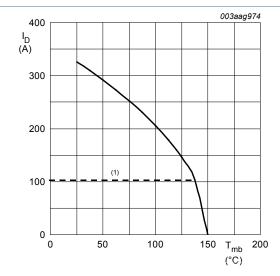


Fig. 1. Continuous drain current as a function of mounting base temperature

$V_{GS} \ge 10 V$
(1) Capped at 100 A due to package.

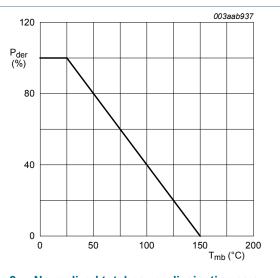
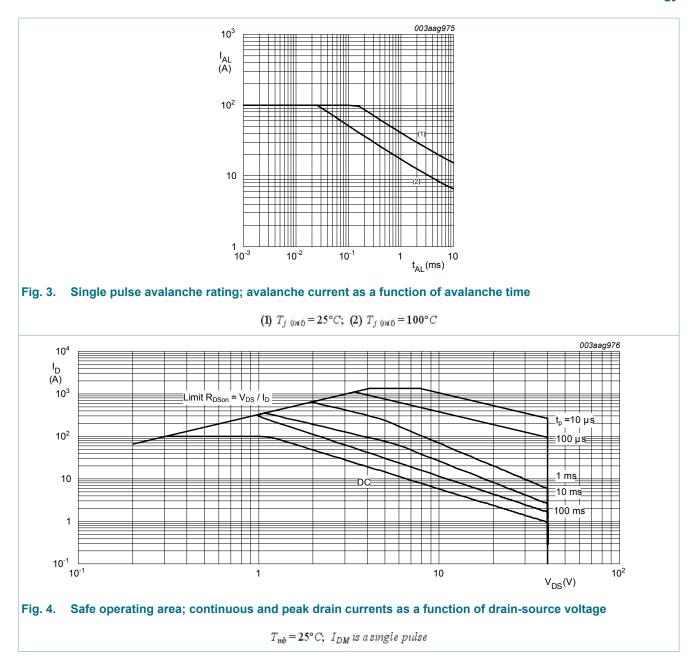


Fig. 2. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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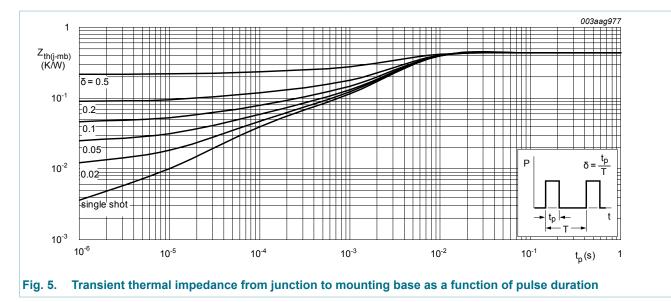
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5. Thermal characteristics

Table 5. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	0.35	0.43	K/W

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6. Characteristics

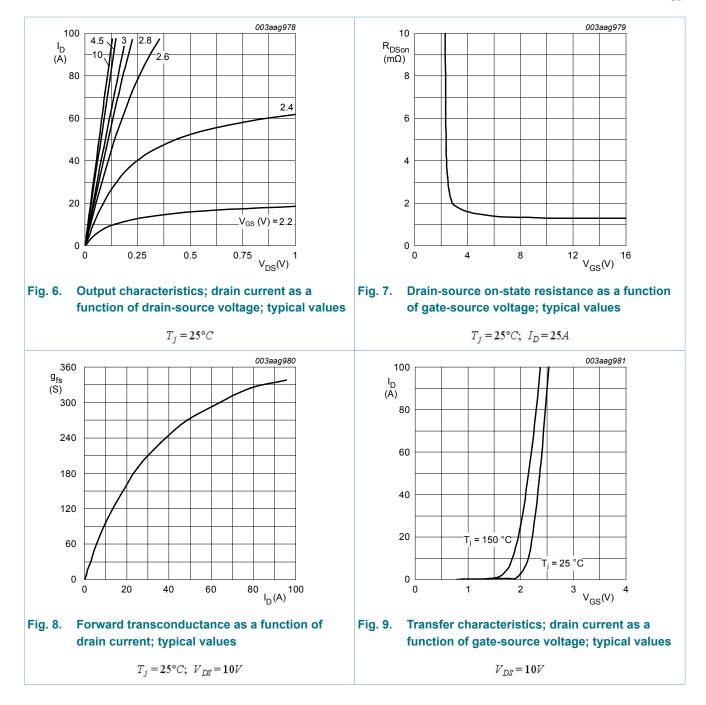
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	1 I				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1.05	1.46	1.95	V
		I _D = 10 mA; V _{DS} = V _{GS} ; T _j = 150 °C	0.5	-	-	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C	-	-	2.25	V
I _{DSS} drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA	
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 150 °C	-	-	100	μA
I _{GSS} gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA	
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 12	-	1.45	1.8	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; Fig. 12; Fig. 13	-	-	3.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 12	-	1.25	1.55	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 12; Fig. 13	-	-	2.7	mΩ
R _G	gate resistance	f = 1 MHz	-	1.17	2.34	Ω

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cł	naracteristics	· · · · · ·				
Q _{G(tot)} total gate charge		I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 14; Fig. 15	-	126	-	nC
	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 14	-	59	-	nC	
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	115	-	nC
Q _{GS}	gate-source charge	I_D = 25 A; V_{DS} = 20 V; V_{GS} = 4.5 V;	-	17.7	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 14	-	12.5	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	5.2	-	nC
Q _{GD}	gate-drain charge		-	15.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 20 V; <u>Fig. 14</u>	-	2.4	-	V
C _{iss}	input capacitance	V _{DS} = 20 V; V _{GS} = 0 V; f = 1 MHz;	-	7790	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	1063	-	pF
C _{rss}	reverse transfer capacitance		-	409	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R _L = 0.8 Ω; V _{GS} = 4.5 V;	-	41	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	48	-	ns
t _{d(off)}	turn-off delay time		-	86	-	ns
t _f	fall time		-	42	-	ns
Q _{oss}	output charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 0 \; V; \; V_{DS} = 20 \; V; \; f = 1 \; MHz; \\ T_{j} = 25 \; ^{\circ}C \end{array}$	-	38.7	-	nC
Source-dra	in diode	· · · · ·	l			
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 17</u>	-	0.77	1.1	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $\text{V}_{DS} = 20 \text{ V}; \text{ Fig. 18}$	-	44	-	ns
Qr	recovered charge	I _S = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 20 V	-	62	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V}; \text{ I}_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{DS} = 20 \text{ V}; \frac{\text{Fig. 18}}{2}$	-	26	-	ns
t _b	reverse recovery fall time		-	18	-	ns

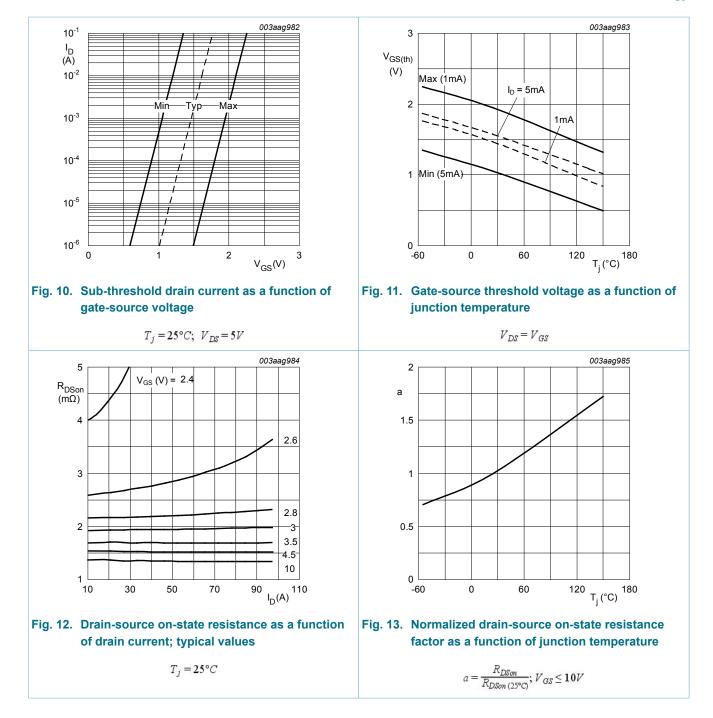
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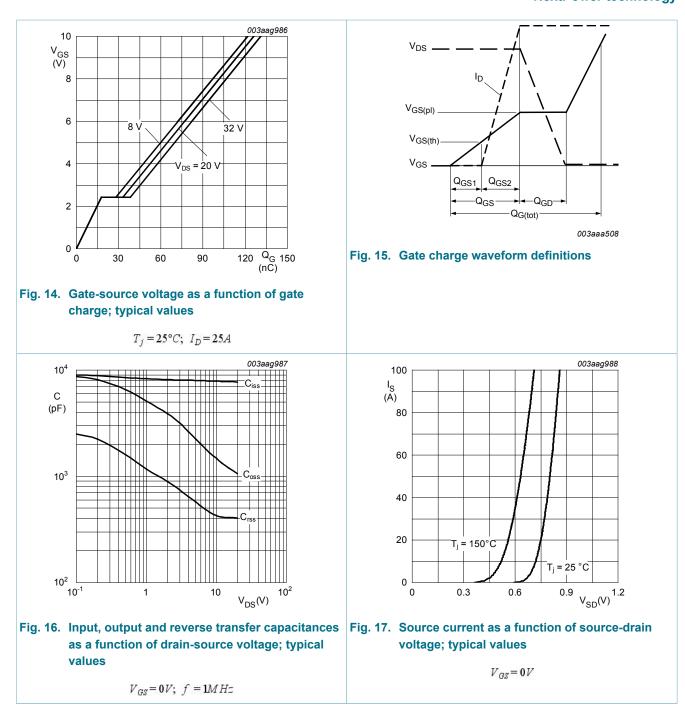
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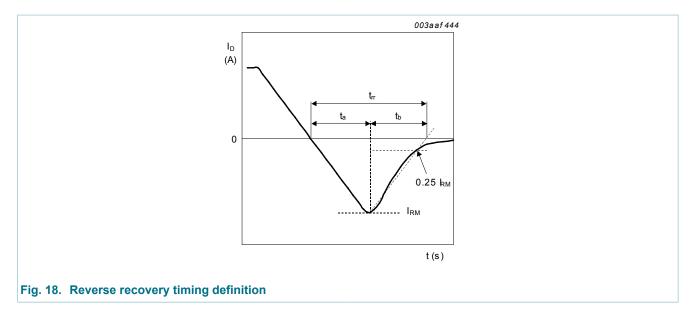
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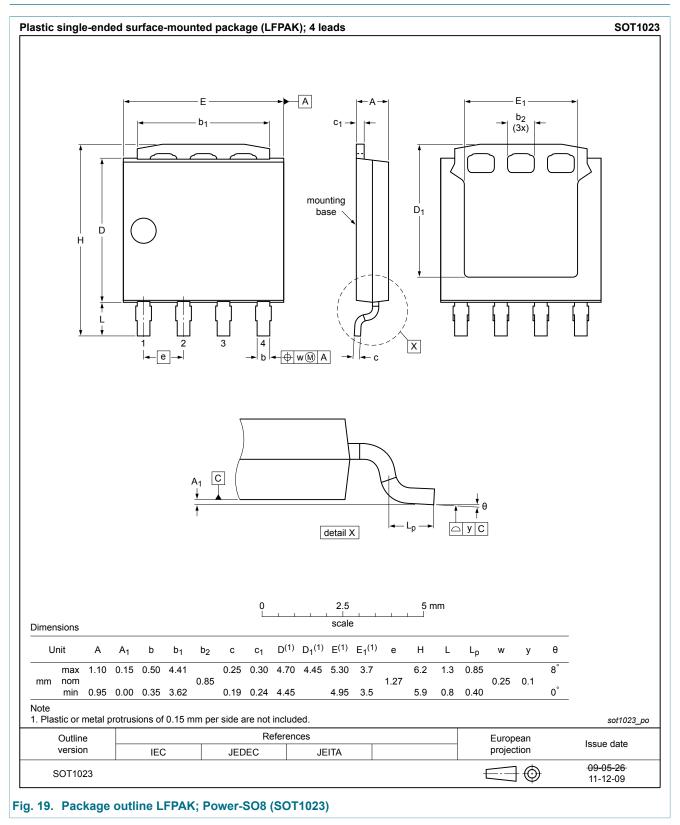
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7. Package outline



PSMN1R6-40YLC

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8. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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